

MAC212A8, MAC212A10

Preferred Device

Triacs

Silicon Bidirectional Thyristors

Designed primarily for full-wave ac control applications, such as light dimmers, motor controls, heating controls and power supplies; or wherever full-wave silicon gate controlled solid-state devices are needed. Triac type thyristors switch from a blocking to a conducting state for either polarity of applied anode voltage with positive or negative gate triggering.

Features

- Blocking Voltage to 800 Volts
- All Diffused and Glass Passivated Junctions for Greater Parameter Uniformity and Stability
- Small, Rugged, Thermowatt Construction for Low Thermal Resistance, High Heat Dissipation and Durability
- Gate Triggering Guaranteed in Four Modes
- Pb-Free Packages are Available*

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

| Rating | Symbol | Value | Unit |
|--|--|-------------|------------------|
| Peak Repetitive Off-State Voltage (Note 1) (T _J = -40 to +125°C, Sine Wave 50 to 60 Hz, Gate Open) MAC212A8 MAC212A10 | V _{DRM} , V _{RRM} | 600 800 | V |
| On-State RMS Current (T _C = +85°C) Full Cycle Sine Wave 50 to 60 Hz | I _{T(RMS)} | 12 | A |
| Peak Non-repetitive Surge Current (One Full Cycle Sine Wave, 60 Hz, T _C = +25°C) Preceded and followed by rated current | I _{TSM} | 100 | A |
| Circuit Fusing Considerations (t = 8.3 ms) | I ² t | 40 | A ² s |
| Peak Gate Power (T _C = +85°C, Pulse Width = 10 μs) | P _{GM} | 20 | W |
| Average Gate Power (T _C = +85°C, t = 8.3 ms) | P _{G(AV)} | 0.35 | W |
| Peak Gate Current (T _C = +85°C, Pulse Width = 10 μs) | I _{GM} | 2.0 | A |
| Operating Junction Temperature Range | T _J | -40 to +125 | °C |
| Storage Temperature Range | T _{stg} | -40 to +150 | °C |

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

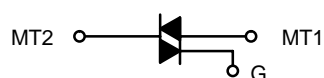
*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



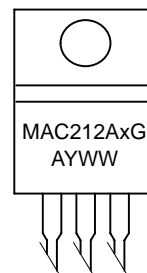
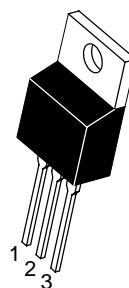
ON Semiconductor®

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TRIACS
12 AMPERES RMS
600 thru 800 VOLTS



MARKING DIAGRAM



TO-220AB
CASE 221A-07
STYLE 4

- x = 8 or 10
- A = Assembly Location
- Y = Year
- WW = Work Week
- G = Pb-Free Package

PIN ASSIGNMENT

| Pin | Assignment |
|-----|-----------------|
| 1 | Main Terminal 1 |
| 2 | Main Terminal 2 |
| 3 | Gate |
| 4 | Main Terminal 2 |

ORDERING INFORMATION

| Device | Package | Shipping |
|------------|-----------------------|-----------------|
| MAC212A8D | TO-220AB | 500 Units / Box |
| MAC212A8DG | TO-220AB (Pb-Free) | 500 Units / Box |
| MAC212A10 | TO-220AB | 500 Units / Box |
| MAC212A10G | TO-220AB (Pb-Free) | 500 Units / Box |

Preferred devices are recommended choices for future use and best overall value.

MAC212A8, MAC212A10

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Value | Unit |
|--|-----------------|-------|-----------------------------|
| Thermal Resistance, Junction-to-Case | $R_{\theta JC}$ | 2.0 | $^{\circ}\text{C}/\text{W}$ |
| Junction-to-Ambient | $R_{\theta JA}$ | 62.5 | |
| Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Secs | T_L | 260 | $^{\circ}\text{C}$ |

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}\text{C}$ unless otherwise noted; Electricals apply in both directions)

| Characteristic | Symbol | Min | Typ | Max | Unit |
|----------------|--------|-----|-----|-----|------|
|----------------|--------|-----|-----|-----|------|

OFF CHARACTERISTICS

| | | | | | |
|--|--------------------------|---|---|-----|---------------|
| Peak Repetitive Blocking Current ($V_D = \text{Rated } V_{DRM}$, V_{RRM} ; Gate Open) | I_{DRM} , I_{RRM} | - | - | 10 | μA |
| $T_J = 25^{\circ}\text{C}$ | | | | | |
| $T_J = +125^{\circ}\text{C}$ | | | | 2.0 | mA |

ON CHARACTERISTICS

| | | | | | |
|--|----------|-----|-----|------|---------------|
| Peak On-State Voltage $I_{TM} = \pm 17 \text{ A Peak}$; Pulse Width = 1 to 2 ms, Duty Cycle $\leq 2\%$ | V_{TM} | - | 1.3 | 1.75 | V |
| Gate Trigger Current (Continuous dc) (Main Terminal Voltage = 12 Vdc, $R_L = 100 \Omega$) | I_{GT} | - | 12 | 50 | mA |
| MT2(+), G(+) | - | 12 | 50 | | |
| MT2(+), G(-) | - | 20 | 50 | | |
| MT2(-), G(-) | - | 35 | 75 | | |
| MT2(-), G(+) | - | | | | |
| Gate Trigger Voltage (Continuous dc) (Main Terminal Voltage = 12 Vdc, $R_L = 100 \Omega$) | V_{GT} | - | 0.9 | 2.0 | V |
| MT2(+), G(+) | - | 0.9 | 2.0 | | |
| MT2(+), G(-) | - | 1.1 | 2.0 | | |
| MT2(-), G(-) | - | 1.4 | 2.5 | | |
| MT2(-), G(+) | - | | | | |
| Gate Non-Trigger Voltage (Continuous dc) (Main Terminal Voltage = 12 V, $R_L = 100 \Omega$, $T_J = +125^{\circ}\text{C}$) All Four Quadrants | V_{GD} | 0.2 | - | - | V |
| Holding Current (Main Terminal Voltage = 12 Vdc, Gate Open, Initiating Current = $\pm 200 \text{ mA}$) | I_H | - | 6.0 | 50 | mA |
| Turn-On Time ($V_D = \text{Rated } V_{DRM}$, $I_{TM} = 17 \text{ A}$, $I_{GT} = 120 \text{ mA}$, Rise Time = $0.1 \mu\text{s}$, Pulse Width = $2 \mu\text{s}$) | t_{gt} | - | 1.5 | - | μs |

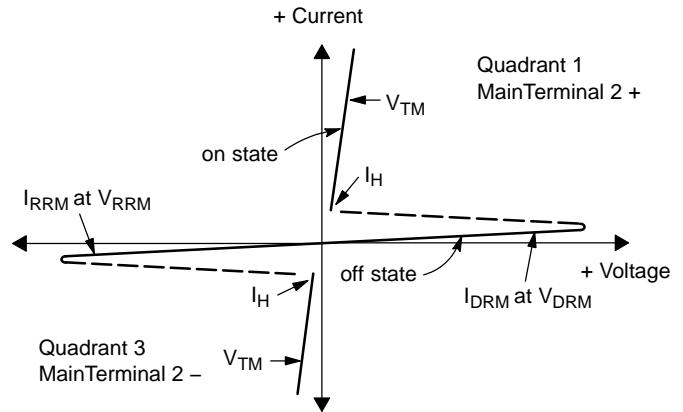
DYNAMIC CHARACTERISTICS

| | | | | | |
|---|---------------|---|-----|---|------------------------|
| Critical Rate of Rise of Commutation Voltage ($V_D = \text{Rated } V_{DRM}$, $I_{TM} = 17 \text{ A}$, Commutating $di/dt = 6.1 \text{ A/ms}$, Gate Unenergized, $T_C = +85^{\circ}\text{C}$) | $dv/dt_{(c)}$ | - | 5.0 | - | $\text{V}/\mu\text{s}$ |
| Critical Rate of Rise of Off-State Voltage ($V_D = \text{Rated } V_{DRM}$, Exponential Voltage Rise, Gate Open, $T_C = +85^{\circ}\text{C}$) | dv/dt | - | 100 | - | $\text{V}/\mu\text{s}$ |

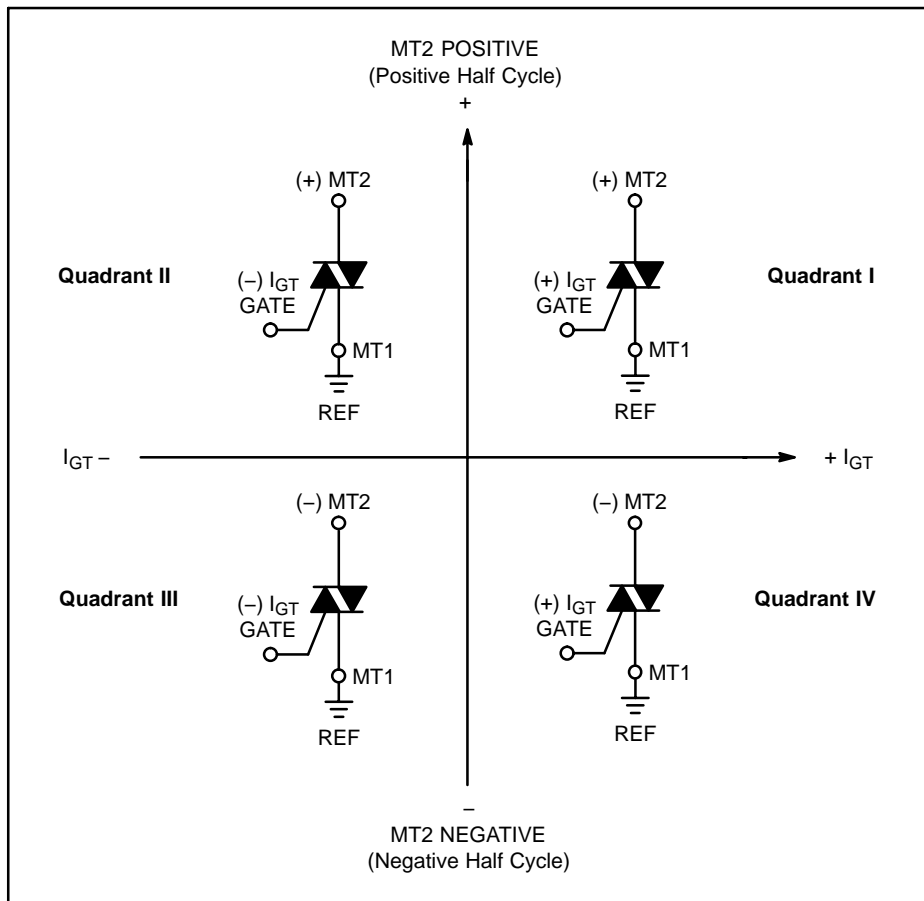
MAC212A8, MAC212A10

Voltage Current Characteristic of Triacs (Bidirectional Device)

| Symbol | Parameter |
|-----------|---|
| V_{DRM} | Peak Repetitive Forward Off State Voltage |
| I_{DRM} | Peak Forward Blocking Current |
| V_{RRM} | Peak Repetitive Reverse Off State Voltage |
| I_{RRM} | Peak Reverse Blocking Current |
| V_{TM} | Maximum On State Voltage |
| I_H | Holding Current |



Quadrant Definitions for a Triac



All polarities are referenced to MT1.
With in-phase signals (using standard AC lines) quadrants I and III are used.

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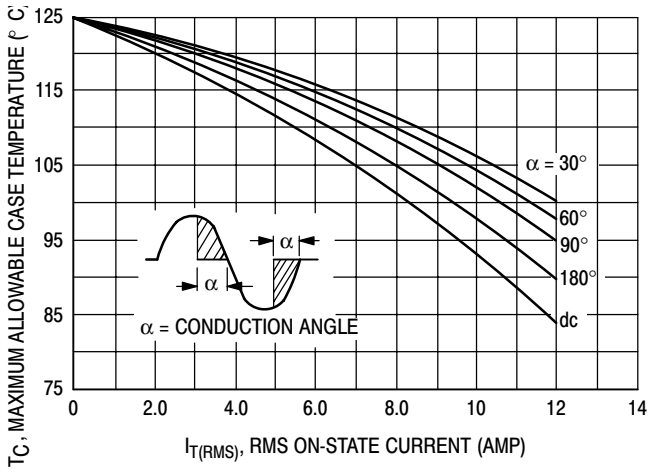


Figure 1. Current Derating

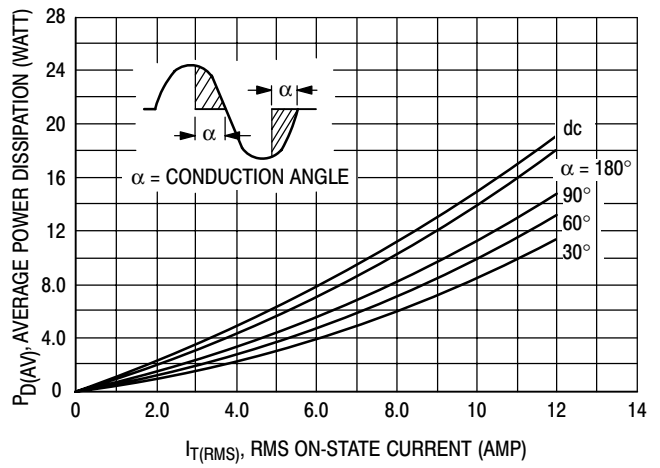


Figure 2. Power Dissipation

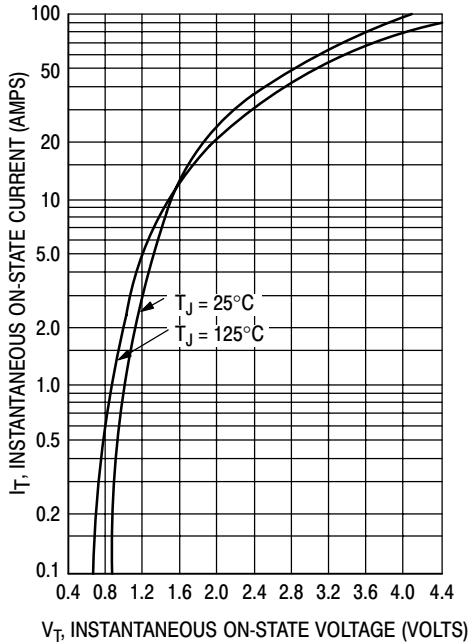


Figure 3. Maximum On-State Voltage Characteristics

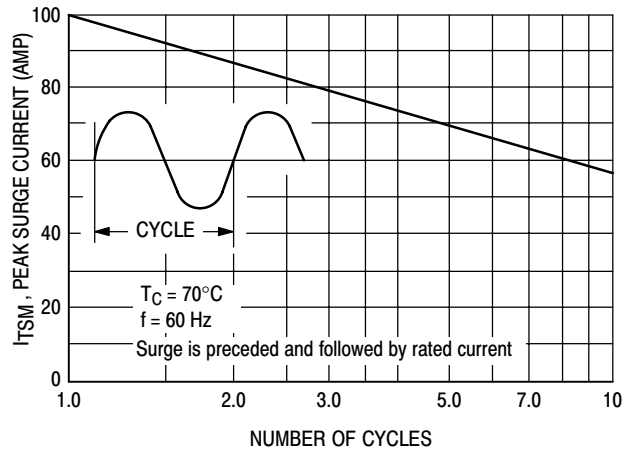


Figure 4. Maximum Non-Repetitive Surge Current

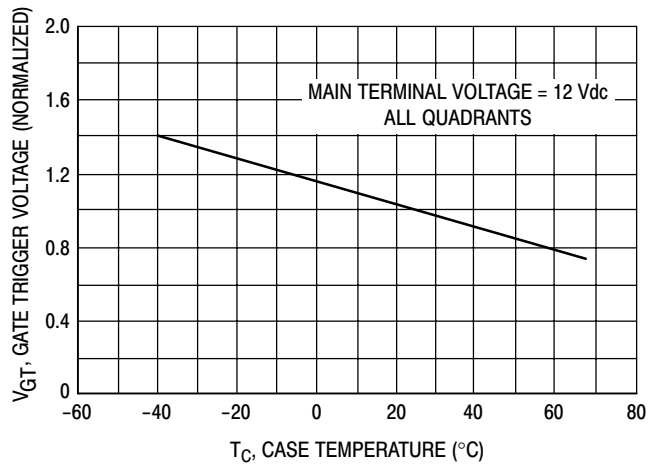


Figure 5. Typical Gate Trigger Voltage

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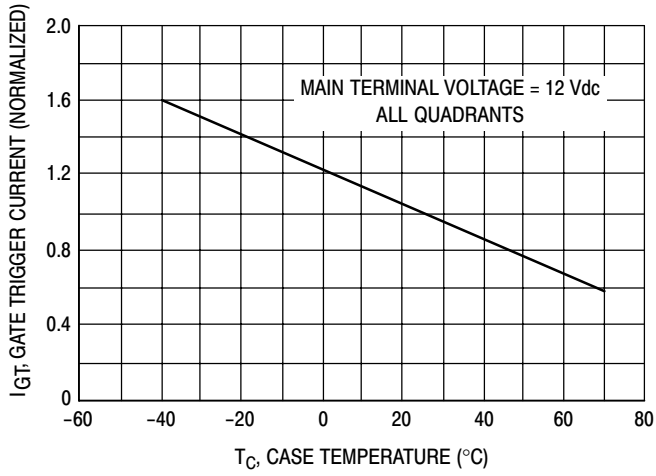


Figure 6. Typical Gate Trigger Current

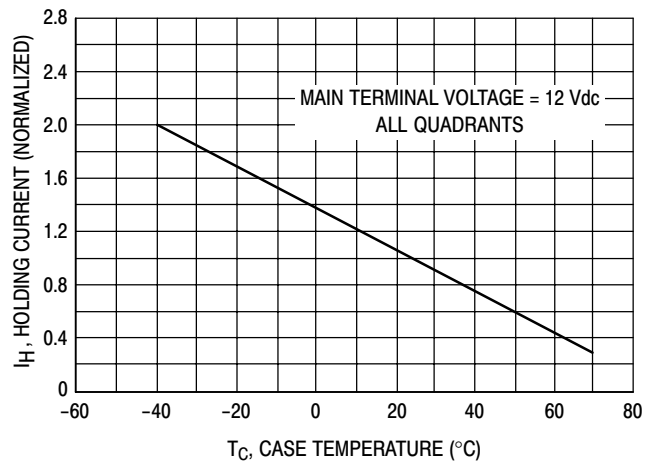


Figure 7. Typical Holding Current

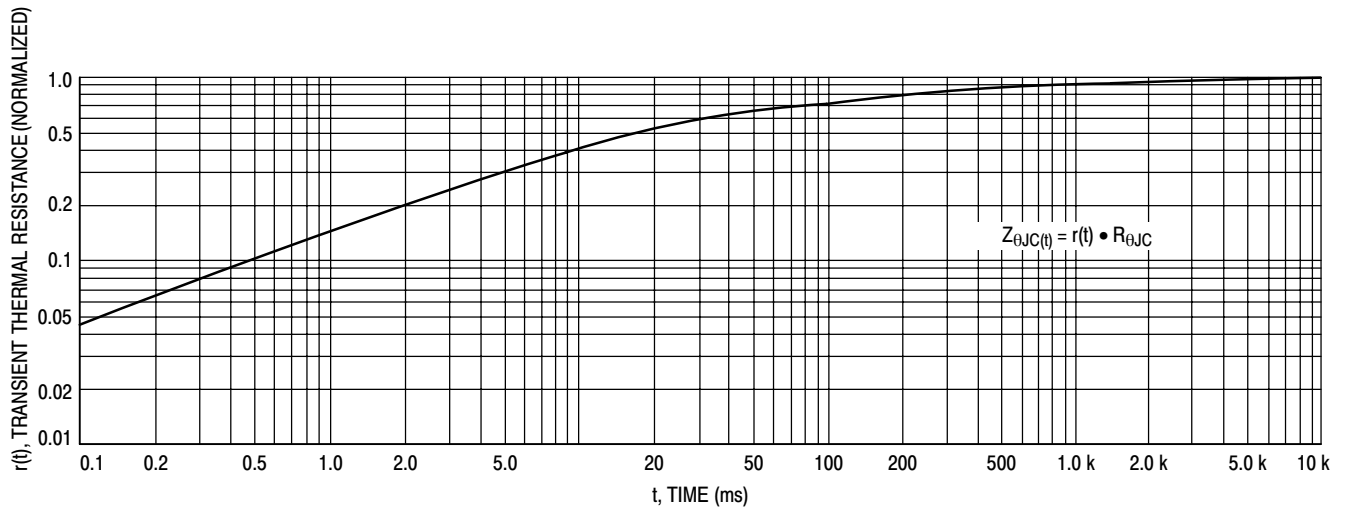
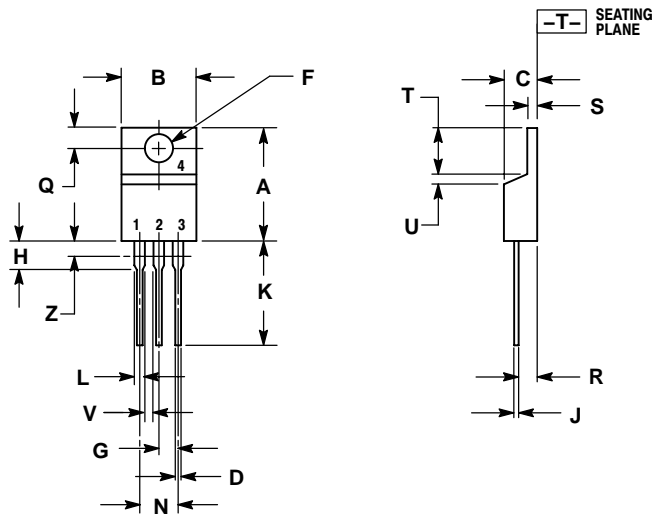


Figure 8. Thermal Response

MAC212A8, MAC212A10

PACKAGE DIMENSIONS

TO-220AB
CASE 221A-07
ISSUE AA



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

| DIM | INCHES | | MILLIMETERS | |
|-----|--------|-------|-------------|-------|
| | MIN | MAX | MIN | MAX |
| A | 0.570 | 0.620 | 14.48 | 15.75 |
| B | 0.380 | 0.405 | 9.66 | 10.28 |
| C | 0.160 | 0.190 | 4.07 | 4.82 |
| D | 0.025 | 0.035 | 0.64 | 0.88 |
| F | 0.142 | 0.147 | 3.61 | 3.73 |
| G | 0.095 | 0.105 | 2.42 | 2.66 |
| H | 0.110 | 0.155 | 2.80 | 3.93 |
| J | 0.014 | 0.022 | 0.36 | 0.55 |
| K | 0.500 | 0.562 | 12.70 | 14.27 |
| L | 0.045 | 0.060 | 1.15 | 1.52 |
| N | 0.190 | 0.210 | 4.83 | 5.33 |
| Q | 0.100 | 0.120 | 2.54 | 3.04 |
| R | 0.080 | 0.110 | 2.04 | 2.79 |
| S | 0.045 | 0.055 | 1.15 | 1.39 |
| T | 0.235 | 0.255 | 5.97 | 6.47 |
| U | 0.000 | 0.050 | 0.00 | 1.27 |
| V | 0.045 | --- | 1.15 | --- |
| Z | --- | 0.080 | --- | 2.04 |

- STYLE 4:
PIN 1. MAIN TERMINAL 1
2. MAIN TERMINAL 2
3. GATE
4. MAIN TERMINAL 2

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